

FILE 'INSPEC' ENTERED AT 12:58:52 ON 29 JUN 2001

L1 132657 S SUBSTRATE
L2 60 S POROUS SEMICONDUCTOR
L3 3735 S POROUS SILICON
L4 2270 S POROUS SI
L5 4187 S L2 OR L3 OR L4
L6 0 S FIRST POROUS LAYER
L7 0 S SECOND POROUS LAYER
L8 1 S FIRST POROSITY
L9 0 S SECOND POROSITY
L10 1 S L6 OR L7 OR L8 OR L9
L11 312 S SEMICONDUCTOR THIN FILM
L12 167 S THIN FILM SEMICONDUCTOR
L13 476 S L11 OR L12
L14 499 S L1 AND L5
L15 0 S L10 AND L14
L16 0 S L13 AND L15

↑

09/616,395

FILE 'INSPEC' ENTERED AT 12:58:52 ON 29 JUN 2001

L1 132657 S SUBSTRATE
L2 60 S POROUS SEMICONDUCTOR
L3 3735 S POROUS SILICON
L4 2270 S POROUS SI
L5 4187 S L2 OR L3 OR L4
L6 0 S FIRST POROUS LAYER
L7 0 S SECOND POROUS LAYER
L8 1 S FIRST POROSITY
L9 0 S SECOND POROSITY
L10 1 S L6 OR L7 OR L8 OR L9
L11 312 S SEMICONDUCTOR THIN FILM
L12 167 S THIN FILM SEMICONDUCTOR
L13 476 S L11 OR L12
L14 499 S L1 AND L5
L15 0 S L10 AND L14
L16 0 S L13 AND L15

FILE 'CAPLUS' ENTERED AT 13:05:20 ON 29 JUN 2001

L17 1 S L16



bib, ab attached

> d bib,ab L17 1-

YOU HAVE REQUESTED DATA FROM 1 ANSWERS - CONTINUE? Y/(N):y

L17 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2001 ACS

AN 2001:62867 CAPLUS

DN 134:122695

TI **Semiconductor thin film substrate**

and method for manufacture thereof using anodic oxidation

IN Ukiya, Noritaka; Nishida, Shoji; Yonehara, Takao; Sakaguchi, Kiyofumi

PA Canon Inc., Japan

SO Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2001023953	A2	20010126	JP 1999-193346	19990707

AB The title **substrate** has a **first porous**

layer, a **second porous layer**, and a

non-porous **semiconductor** layer, wherein a layer which

has a region less porous than the first and second porous layers and a region more porous than the first and second porous layers. The porous layers are formed by anodic oxidn. of the non porous layer. The

semiconductor thin film is produced in short

time and the semiconductor **substrate** material is easily used

again. The **semiconductor thin film** is

suitable for use in a solar cell and a photosensor.